

IWORID

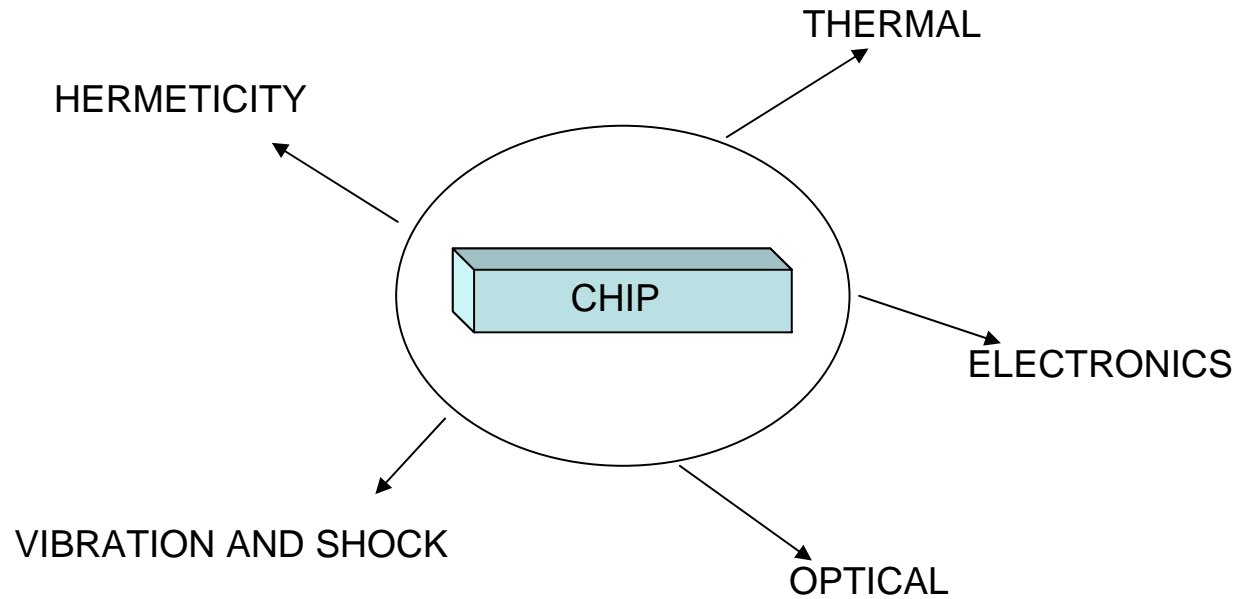
July 5th 2005, ESRF, GRENOBLE

FLIP CHIP INTEGRATION: STATUS AND FUTUR TRENDS

- INTRODUCTION
 - What is packaging, the different levels
 - Evolution of packaging
 - The Flip chip technology
- DIFFERENT FLIP CHIP METHODS
 - Associated technologies
 - Advantages and Limitations
- INNOVATIVE TECHNOLOGIES

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What is Packaging



Different packaging levels

Level 0 : Silicon Chip

- Integrated Circuit etched on a Silicon Wafer

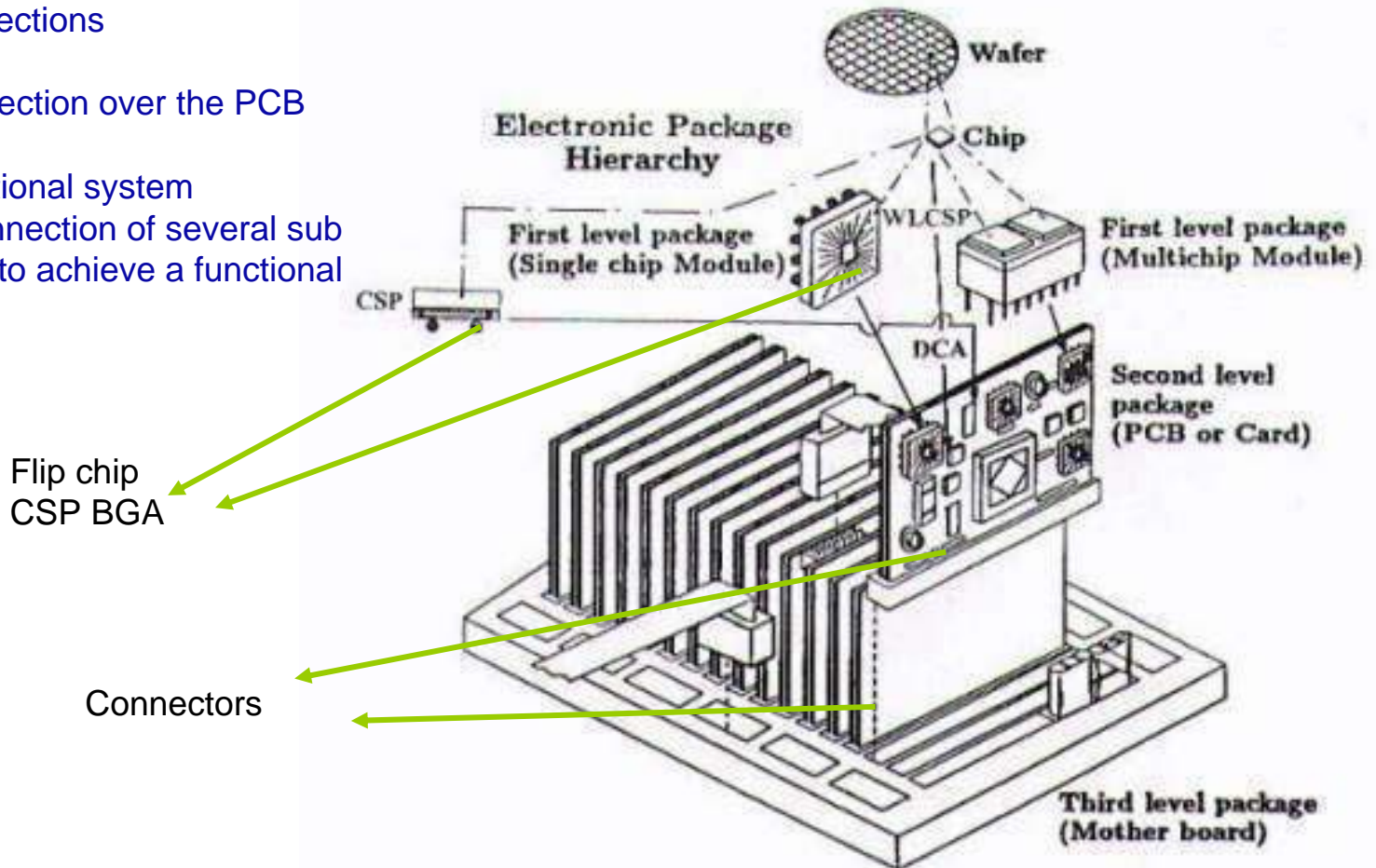
Level 1 ; « Chip Carrier »

- Ceramic or Plastic Encapsulent with electrical connections

Level 2 : Connection over the PCB

Level 3 : Functional system

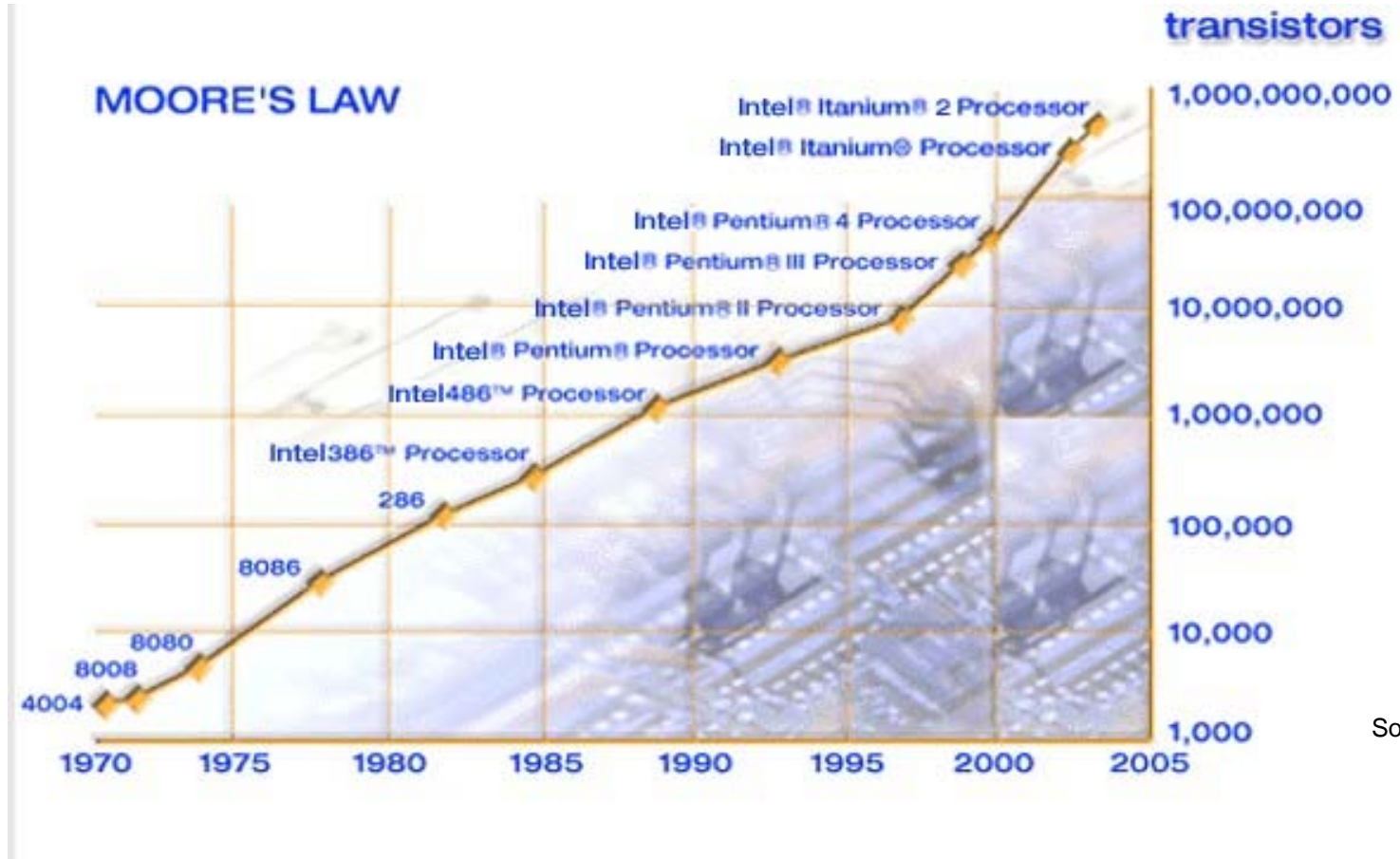
- interconnection of several sub systems to achieve a functional system



Source: TUMALA

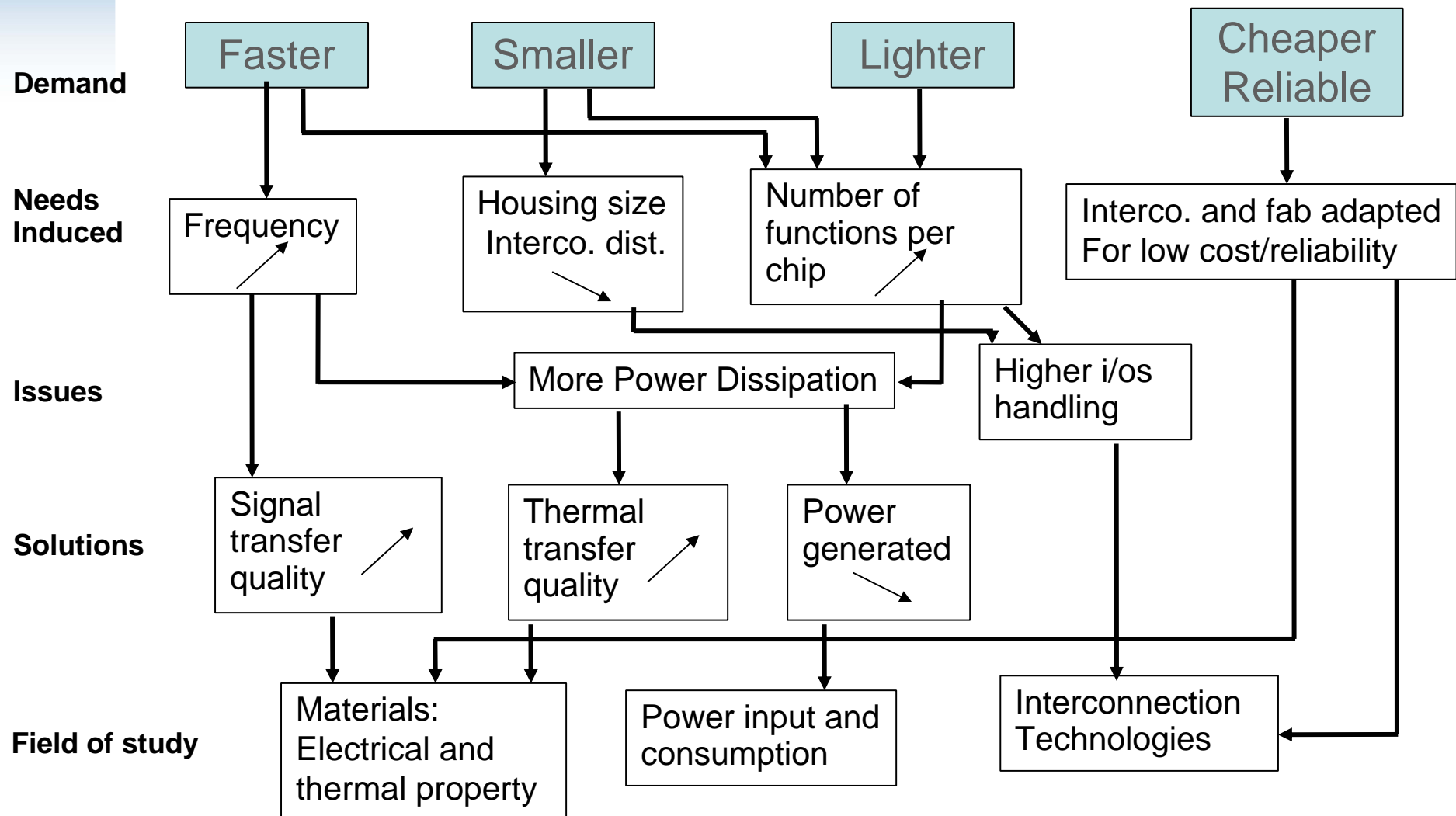
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Increased Chip Density



Source Intel

Packaging: New Requirements

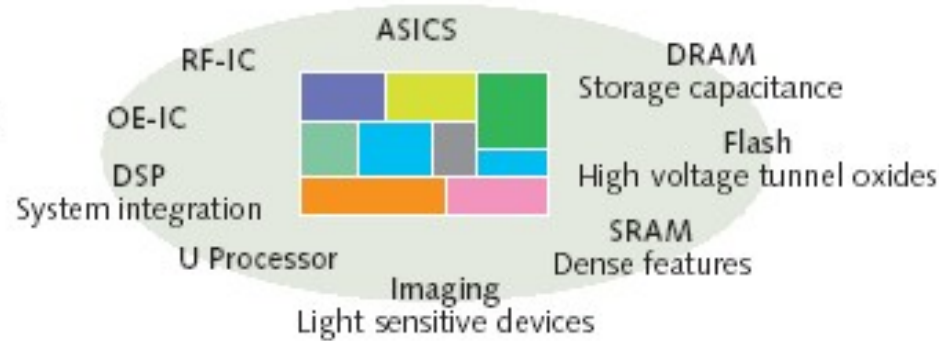


Source: M. Massena

SOP, SiP, MCM, SOC : lots of solutions

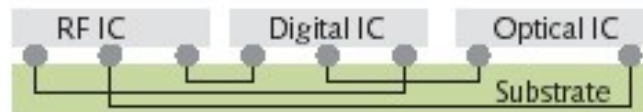
SOC

Complete system on one chip



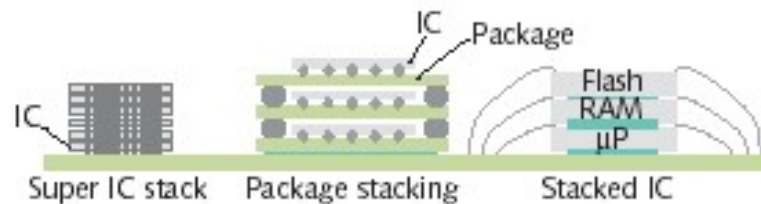
MCM

Interconnected components



SIP

Stacked chip/package



SOP

- Optimizes functions between ICs and package
- Miniaturizes systems



Best of Both IC & Package

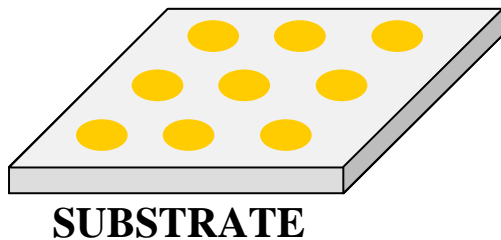
Source Georgia Tech

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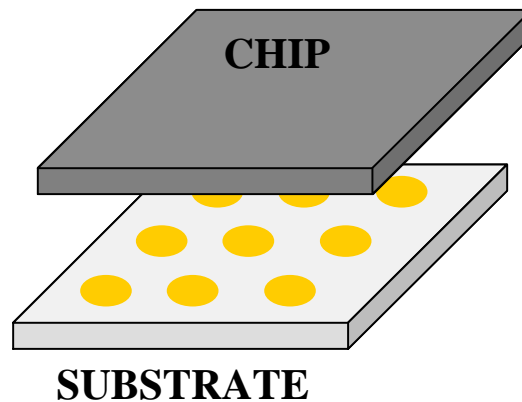
What is Flip Chip

- **Face down** Electrical connection
- Chip over a substrate
- **Array** type connection (Not peripheral) using **bumps**
- Usually with an **underfill** (Reliability)

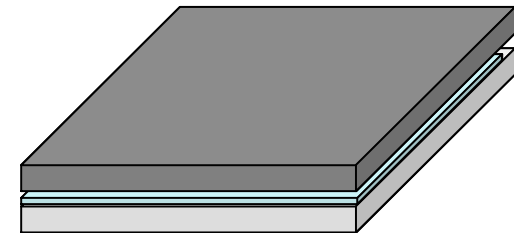
Bumps Fabrication



Assembly



Underfilling

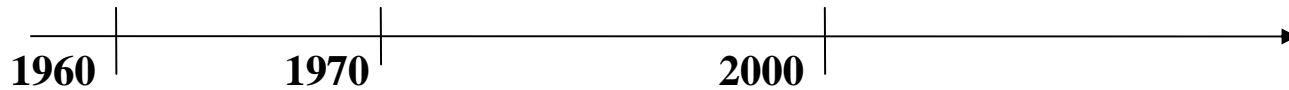


A little bit of History

- Flip chip: invented by IBM in early 60's
Controlled Collapse Chip Connection (C4- 1964)

Flip chip Invented

3% wafers produced
worldwide used for
flip chip

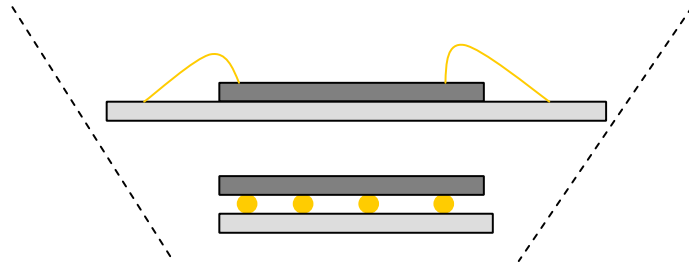


Underfill introduced

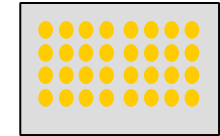
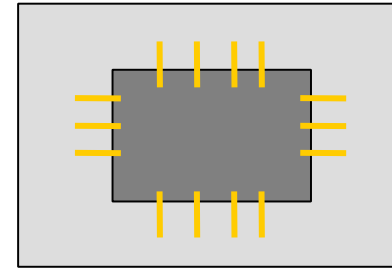
10% wafers produced
expected to be used for
flip chip

Flip Chip vs Wire Bonding

SIZE REDUCTION



NUMBER OF I/O's



Smaller pitch

- **Flip Chip**

- Size reduced
- Higher integration
- Shorter connection length
- Smaller pitch
- Self alignment
- collective process
- Efficient heat dissipation

- **Wire Bonding**

- Industrially proven
- Moderate cost
- Reliability
- Compatibility (housings, connectors)
- Standard metallurgy (no post process)

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Flip Chip : The different techniques

- Solder bump Flip Chip
- Stud bump Flip Chip
- Polymer bump Flip Chip
- Anisotropic Conductive film Flip Chip

Chip over circuit



Chip and circuit over a substrate



Solder Bump Flip Chip: The different steps

- ASIC and chip Post Process
- Solder bump deposition
- Solder Reflow
- Flip Chip assembly
- Underfilling

Solder Bump Flip Chip: The Post Process

Sputtering Deposition

3 Metal layers deposited



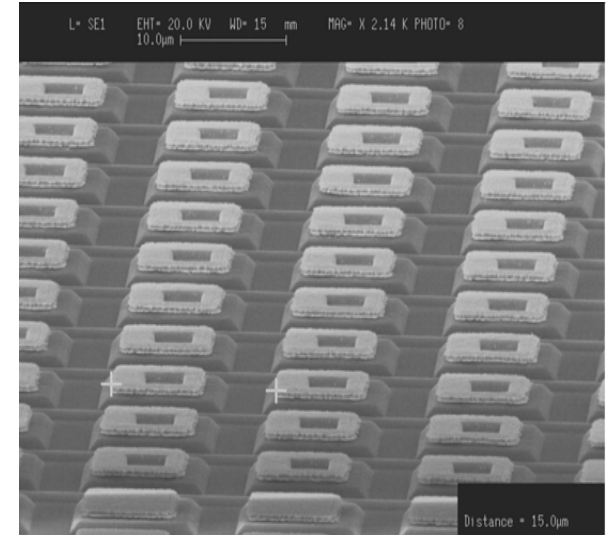
Lithographie



Metal Etching

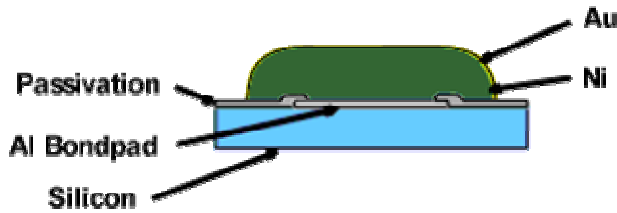


15 μm pitch Ti/Pd/Au UBM

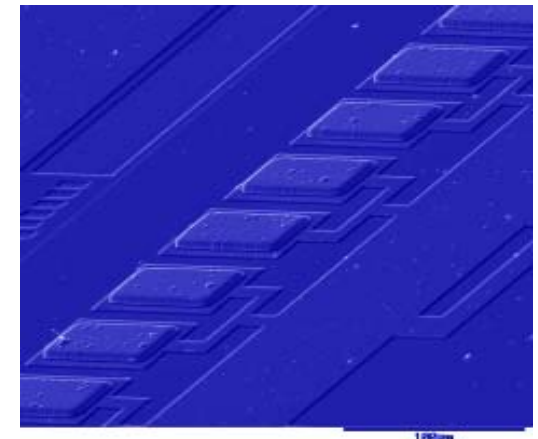


Source: LETI

Electroless deposition (NiAu)



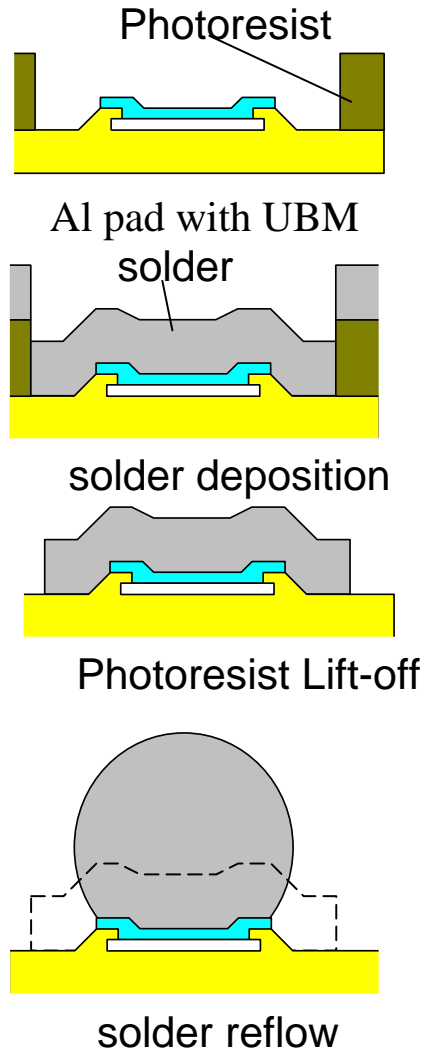
1 μm to 30 μm Ni
0,05 μm Au



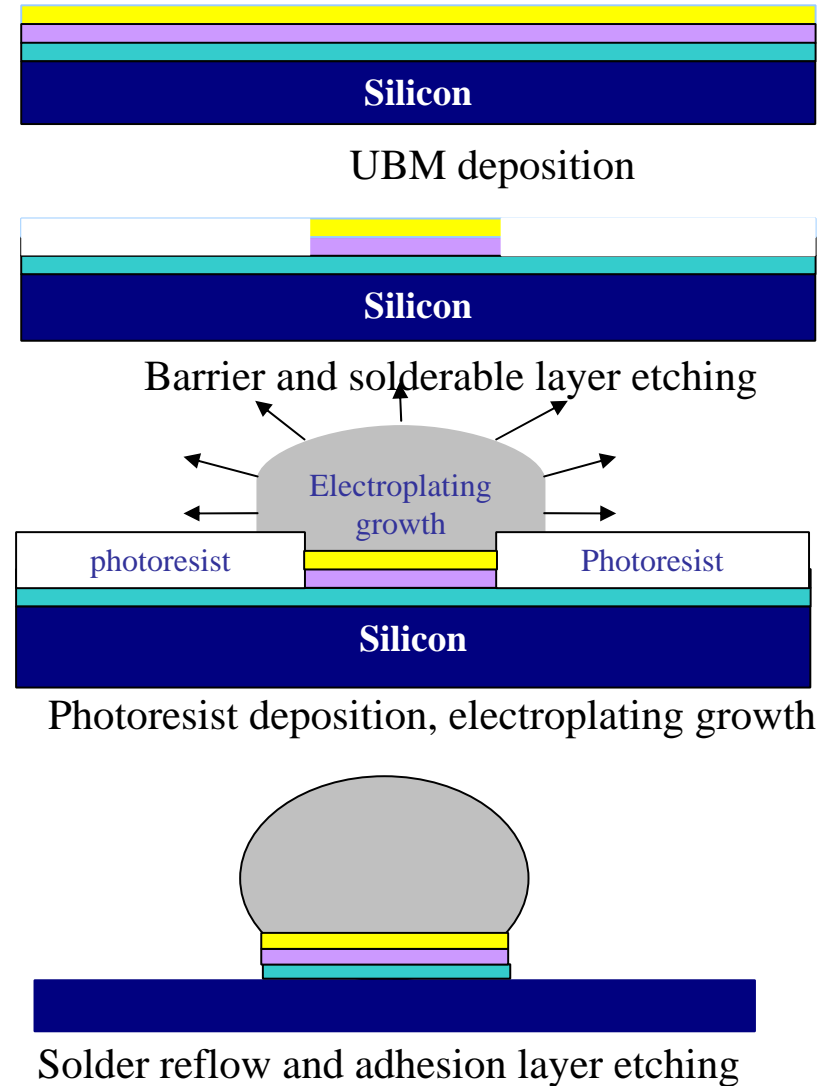
Source: Pac Tech

Solder deposition and Solder Reflow

Evaporation Method

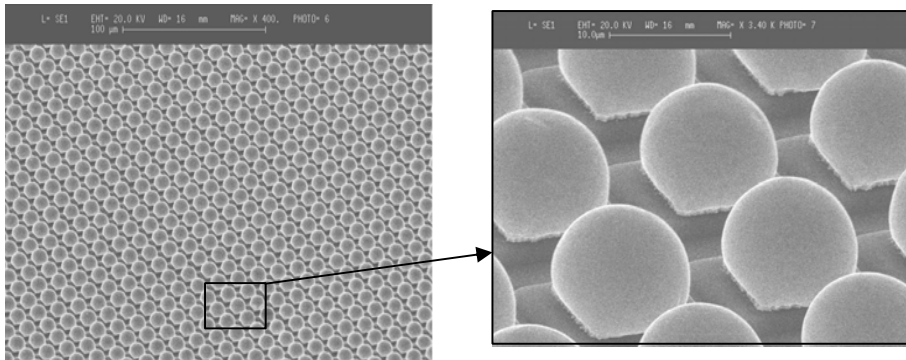


Electroplating Method



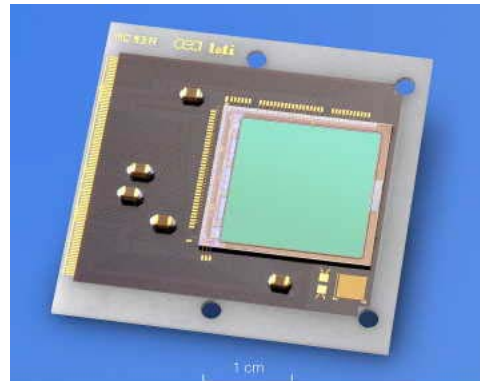
Solder deposition and Solder Reflow

Example of indium vapor deposition at leti



Méga Pixel IRFPA 1024 x 1024 : pitch = 15 µm

Indium Micro-bumps
(SEM Photography)



Spectral band: 3 - 5 µm -
Cutoff frequency: 5.5 µm



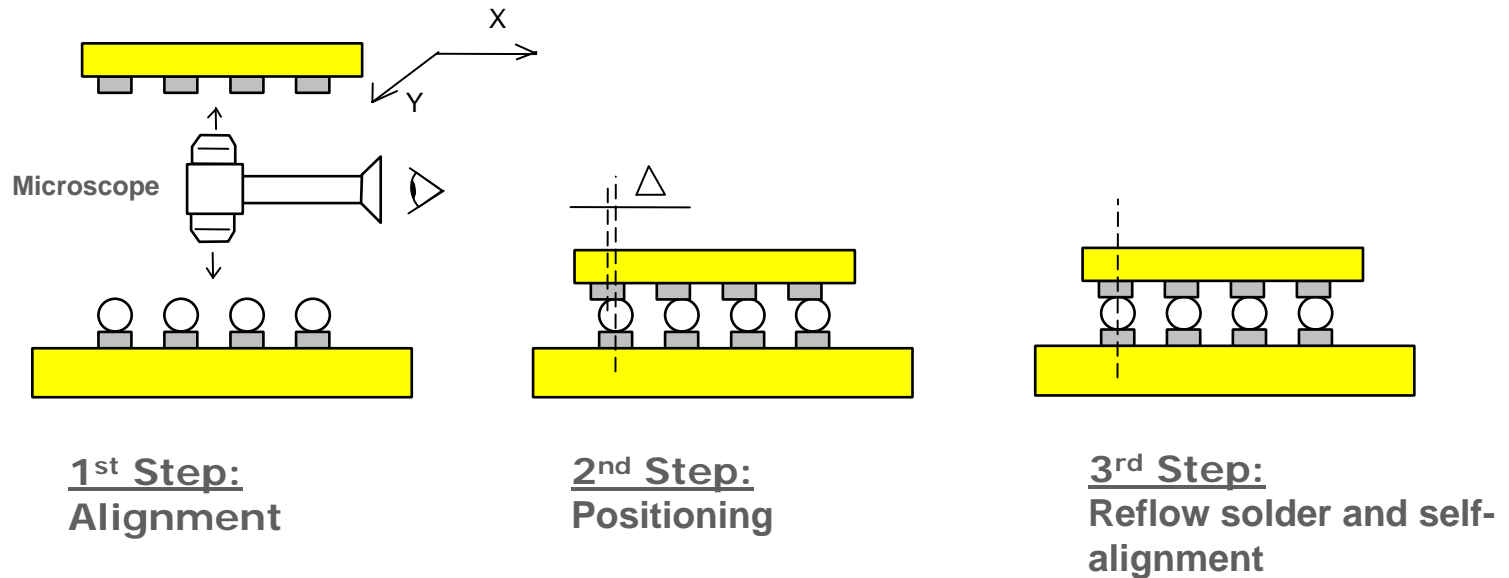
Night view
Operability 99.8%
NETD 20mK

Solder deposition method comparison

	Advantages	Disadvantages	Size
• Evaporation	- thin film process uniformity, flexibility	- cost, time	10 μ -100 μ
• Electroplating	- low cost, fine pitch	- flexibility	10-200 μ
• Screen Printing	- cost, simplicity production	- pitch limitation	150-1000 μ
• Jet printing	- limited number of Bumps, no mask	- pitch limitation	> 150 μ

Solder Flip Chip Assembly

A three step process

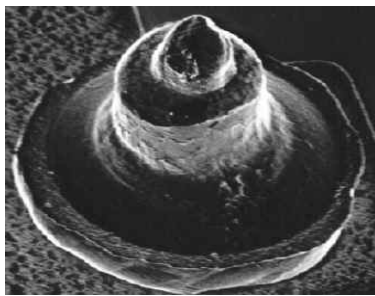


- Temperature process: CTE mismatch
- Flux activated process: cleaning issues
- Large chip size: constraint, shear stress, reliability issues
- Yield: underfilling step necessary

Flip Chip using Stud Bump

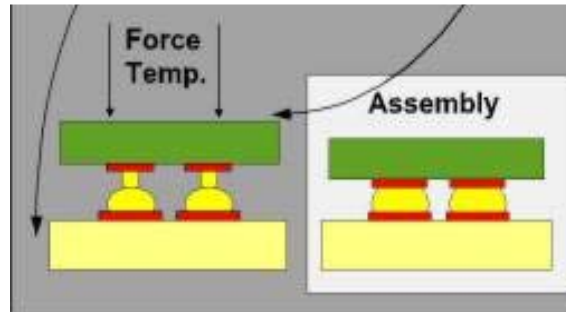
- Conductive gold bumps on the die
- Directly on the Al pad
- Thermomechanical or Adhesive attachment

Gold Stud Bump

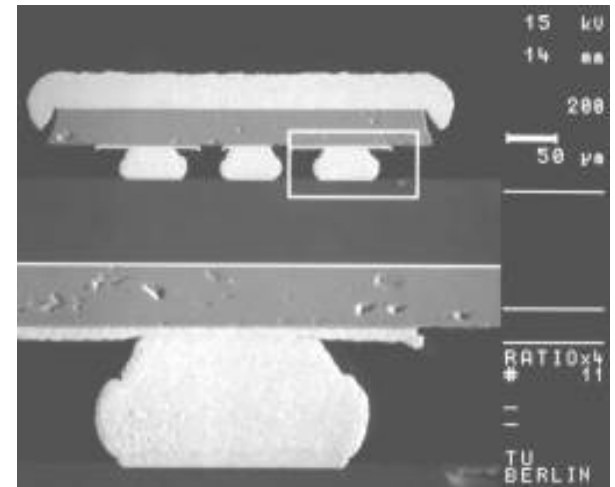


Source: www.flipchips.com

Thermocompression assembly



Source: IZM



Stud Bump Flip Chip:

Advantages

- No wafer post process
- Bumping equipment widely available
- No fluxing

Limitations

- Serial process (low to medium volume production, 24 bumps/sec.)
- No self-alignment
- Minimum Pitch 50-60 μm
- High Temperature & Force applied

Principle

- Conductive particles filled adhesive
- Particles: Typically Silver

Dispense

- Dispensing
- Screen Printing

Assembly

- Curing

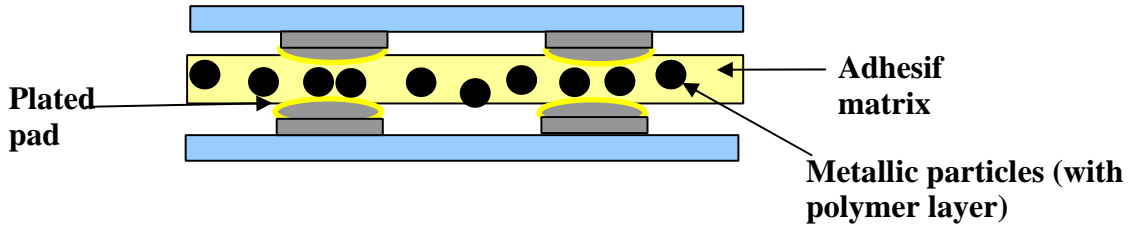
Advantages

- Low temperature process
- Low cost

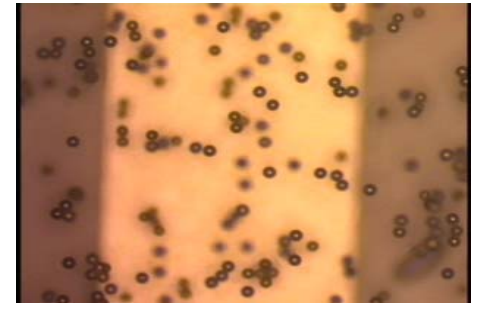
Flip Chip with Anisotropic Conductive Film

different types:

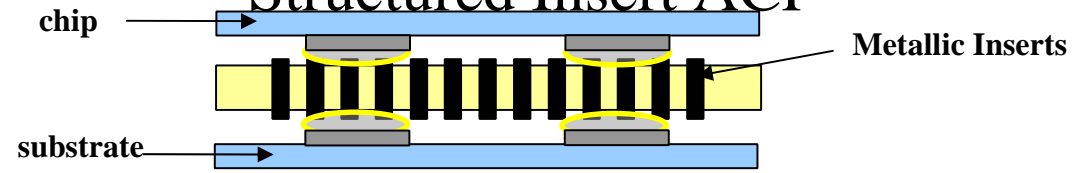
Trapped particles ACF



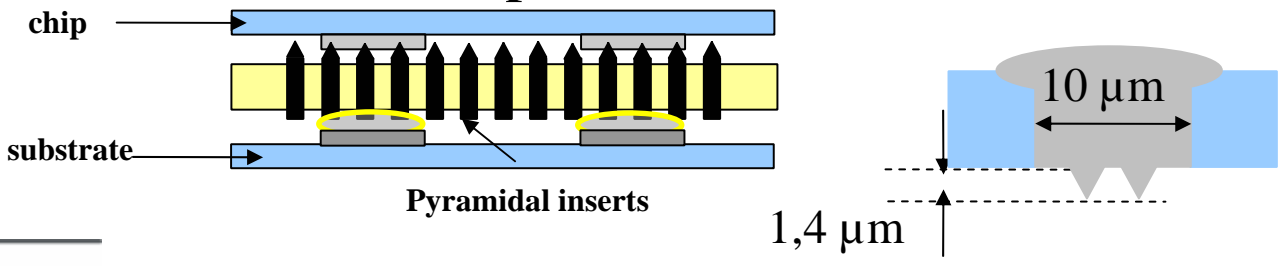
5552 R Film **3M**



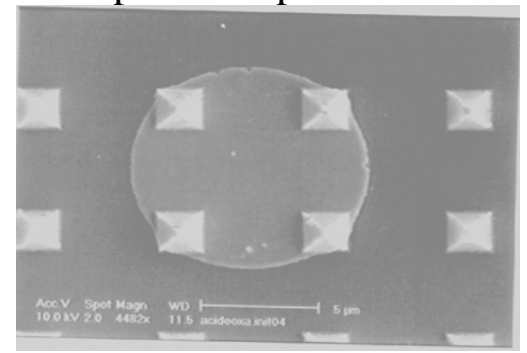
Structured Insert ACF



Micro tips insert ACF



Micro tips developed at LETI



Advantages

- No underfilling step
- Low temperature process (100°C)
- No post process with micro tips inserts

Limitations

- Fine pitch
- Post process
- No self alignment
- Pressure applied
- Electrical contact

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Issues and Limitations

- CTE Mismatch
 - Size limitation
 - Reliability issues
- Small Pitch
 - Alignment
 - Cleaning
- Yield
 - No inspection possible
- Circuit tiling
 - Need solution for 3D Interconnection
- Cost

Comparison of the Different Methods

	DISPENSE AND PROCESS	PITCH	CONTACT RESISTANCE	ASSEMBLY AND TEMPERATURE	RELIABILITY	COST
SOLDER FLIP CHIP	Screen printing, Electroplating, vapor deposition, jet dispensing. Post process required	150µm 15 µm and over	1.2 mΩ	Depends on solder Reliable low temperature solder: In 180°C process Self alignment Cleaning required	Reliable with underfilling Repairable	Depends on solder Expensive with In
STUD BUMP FLIP CHIP	Standard wire bonding equipment No post process	60 µm		Over 200°C Pressure applied (75to100g/bumps) No self alignment No cleaning	Reliable Not repairable	40\$/wafer with 250000 bumps/wafer source: flipchips.com
POLYMER FLIP CHIP	Screen printing, dispensing Post process required	125 µm	5-10 mΩ	<100°C No self alignment No cleaning	Limited reliability for dense connection Not repairable	Low cost
ACF	Commercially available films Post process required	50µm	50 mΩ (with 10 particles/pads)	100°C Pressure applied (15-30 kg/cm ²) No self alignment No cleaning required	Limited reliability for dense connection Not repairable	Low cost

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New Flip Chip approach: Nano-connections

- Carbon Nanotubes (Georgia Tech)
- Copper Nanotubes (Georgia Tech)

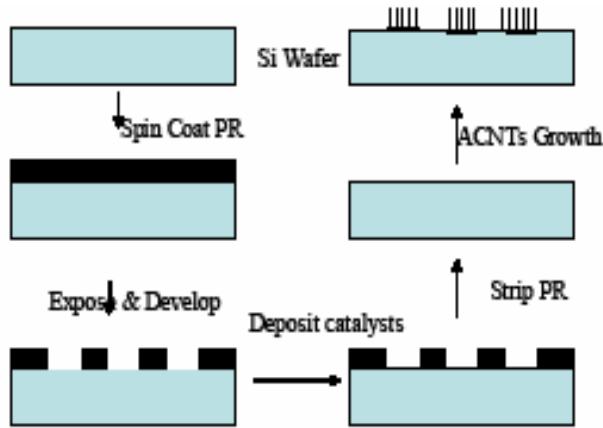


Fig. 6. Scheme of the CNT pillar growth

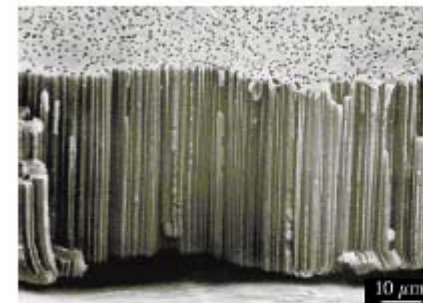
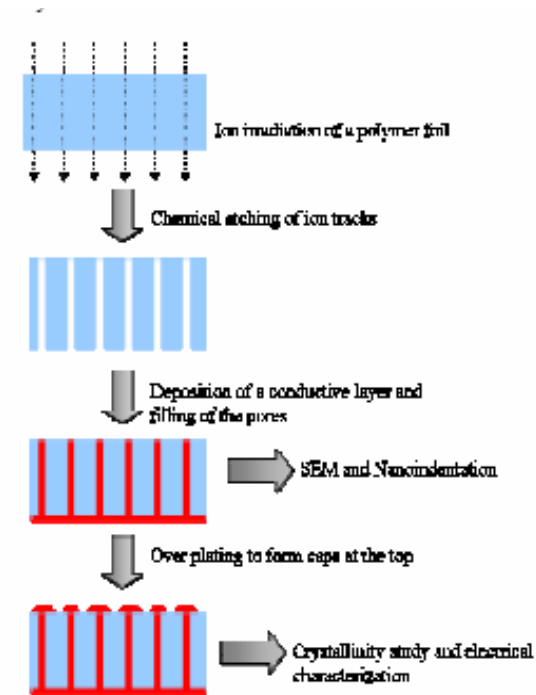
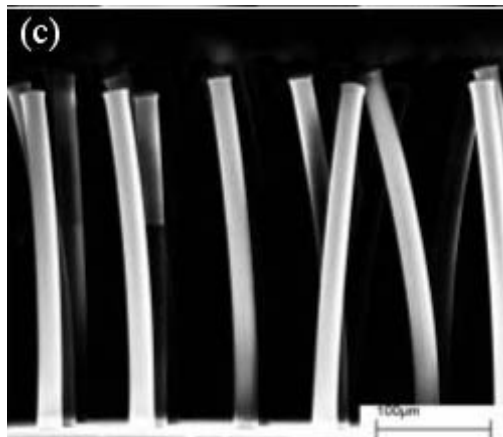
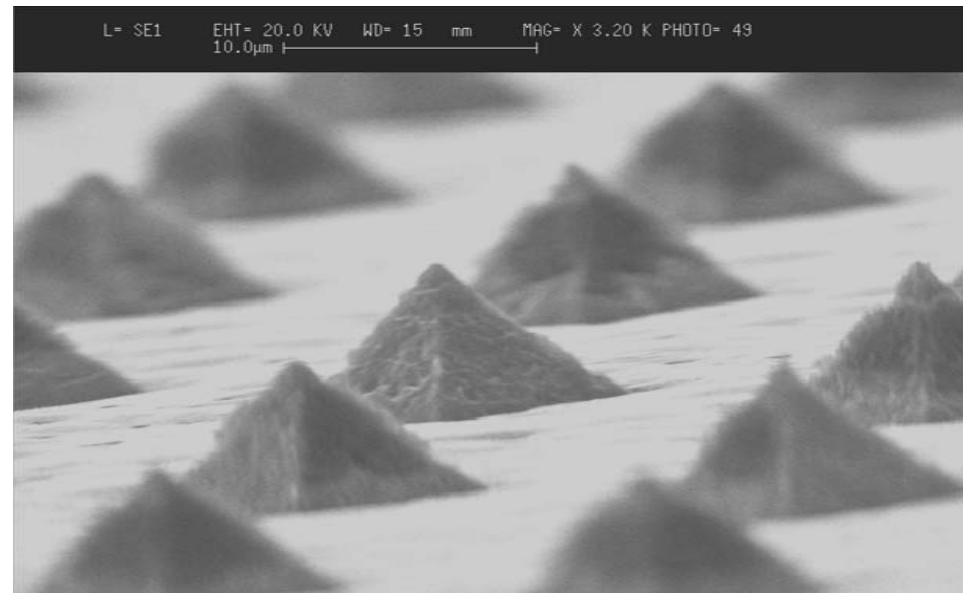


Figure 2: SEM image of side view of the etched polymeric membrane

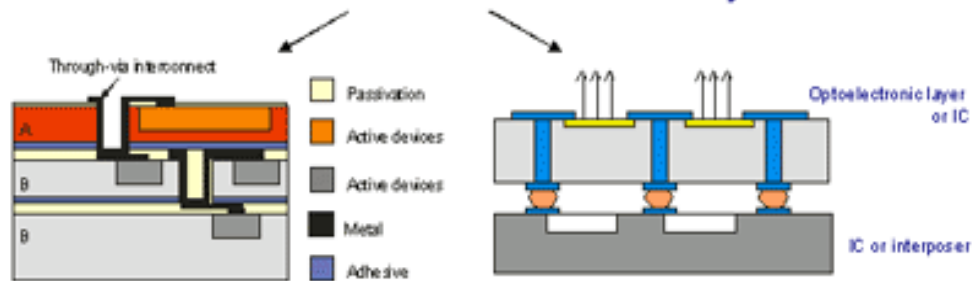
- Solder Micro Tips (LETI)
 - Fabrication demonstrated
 - Assembly tested
 - Fluxless assembly
 - No underfill



3D-Interconnections

- Based on through vias filled with metal (Cu)
- Strong technical challenges (vias, vertical wall metalization and passivation)
- Cell phone application (Japan)
- Exemple: MCNC Research Center:

Vertical Interconnects Can be Used in Two Ways



Stacking of Device Layers

Typically:

- via diameter 5-10 μm
- Via pitch 25-50 μm
- Device layer thickness 20-50 μm

Backside contacts w/flip chip

Typically:

- via diameter 50-100 μm (bond pad)
- Via pitch dependent on application
- Wafer thickness 300-500 μm

Via Aspect Ratio 5-10

Conclusion: Future Integration Trends

- **Total Integration with SOC**
 - Very complexe
 - Mix backend and frontend technologies

- **Development of Wafer Level Packaging and SIP**
 - More and more heterogeanous functions on the same substrate (MEMES, MOEMS, IC's)
 - Denser packaging: 3D connections

- **New connection technique for Flip Chip assembly**

Thanks for your attention

QUESTIONS ?